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December 2013

## FDPF8N50NZU N-Channel UniFET<sup>™</sup> II Ultra FRFET<sup>™</sup> MOSFET **500 V, 6.5 A, 1.2** Ω

## Features

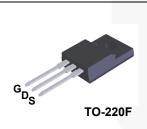
- R<sub>DS(on)</sub> = 1.0 Ω (Typ.) @ V<sub>GS</sub> = 10 V, I<sub>D</sub> = 3.25 A
- Low Gate Charge (Typ. 14 nC)
- Low C<sub>rss</sub> (Typ. 5 pF)
- 100% Avalanche Tested
- Improved dv/dt Capability
- ESD Improved Capability
- RoHS Compliant

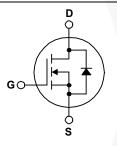
## Applications

- LCD/LED TV
- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply

## Description

UniFET<sup>™</sup> II MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on advanced planar stripe and DMOS technology. This advanced MOSFET family has the smallest on-state resistance among the planar MOSFET, and also provides superior switching performance and higher avalanche energy strength. In addition, internal gate-source ESD diode allows UniFET II MOSFET to withstand over 2kV HBM surge stress. UniFET II Ultra FRFET™ MOSFET has much superior body diode reverse recovery performance. Its t<sub>rr</sub> is less than 50nsec and the reverse dv/dt immunity is 20V/nsec while normal planar MOSFETs have over 200nsec and 4.5V/nsec respectively. Therefore UniFET II Ultra FRFET MOSFET can remove additional component and improve system reliability in certain applications that require performance improvement of the MOSFET's body diode. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





## Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol		Parameter	FDPF8N50NZU	Unit		
V <sub>DSS</sub>	Drain to Source Voltage			500	V	
V <sub>GSS</sub>	Gate to Source Voltage			±25	V	
ID	Drain Current	- Continuous (T <sub>C</sub> = 25 <sup>o</sup> C)		6.5*	Δ.	
	Drain Current	- Continuous (T <sub>C</sub> = 100 <sup>o</sup> C)	/	3.9*	A	
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	26*	Α	
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)			80	mJ	
I <sub>AR</sub>	Avalanche Current		(Note 1)	6.5	Α	
E <sub>AR</sub>	Repetitive Avalanche Ener	ду	(Note 1)	13	mJ	
dv/dt	Peak Diode Recovery dv/dt (			20	V/ns	
P <sub>D</sub>	Dower Dissinction	(T <sub>C</sub> = 25 <sup>o</sup> C)		40	W	
	Power Dissipation	- Derate Above 25°C		0.32	W/ºC	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	°C	

\*Drain current limited by maximum junction temperature

## **Thermal Characteristics**

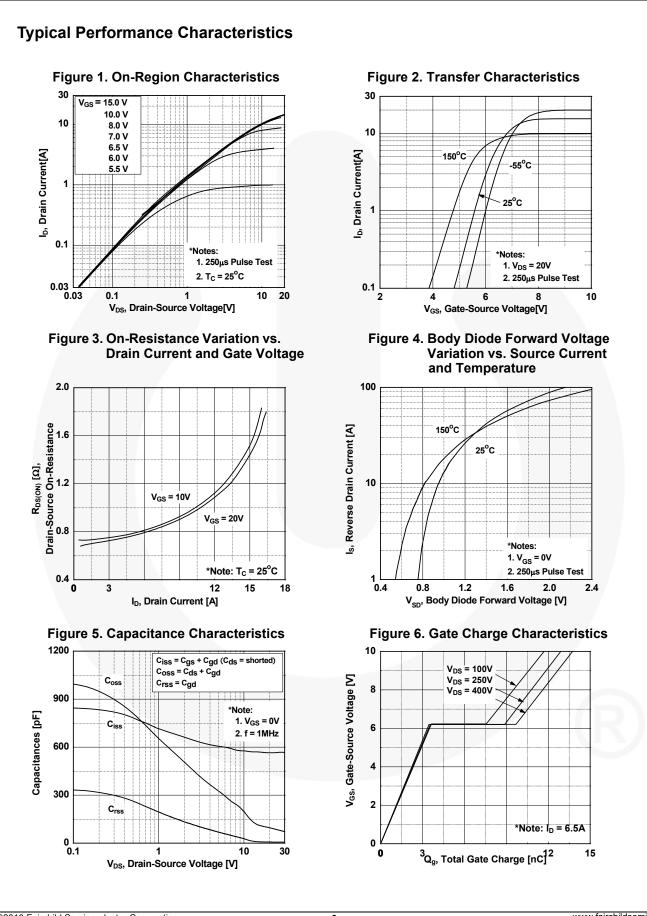
Symbol	Parameter	FDPF8N50NZU	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	3.1	
$R_{\theta CS}$	Thermal Resistance, Case to Sink, Typ.	0.5	
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

· · · · · · · · · · · · · · · · · · ·		Package	Packing Method	Reel Size	Тар	e Width	Qua	intity	
		TO-220F	220F Tube N/A		N/A		50 units		
Electrica	l Char	acteristics T <sub>c</sub> = 25	°C unless otherwis	se noted.					
Symbol	ol Parameter			Test Conditions		Min.	Тур.	Max.	Unit
Off Charac	teristic	S							
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage		age Ir	I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V, T <sub>C</sub> = 25 <sup>o</sup> C		500	-	-	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient		<b>`</b>	$I_D = 250 \mu A$ , Referenced to $25^{\circ}C$		-	0.5	-	V/°C
	Zoro Co			$V_{DS} = 500V, V_{GS} = 0V$ $V_{DS} = 400V, T_{C} = 125^{\circ}C$		-	-	25	μΑ
IDSS	Zero Gate Voltage Drain Current		V			-	-	250	
I <sub>GSS</sub>	Gate to	Body Leakage Current	V	$V_{\rm GS}$ = ±25V, $V_{\rm DS}$ = 0V		-	-	±10	μA
On Charac	teristic	5							
V <sub>GS(th)</sub>	Gate Threshold Voltage			/ <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250μA		3.0	_	5.0	V
R <sub>DS(on)</sub>	Static Drain to Source On Resistance			$V_{GS} = 10V, I_D = 4A$		-	1.0	1.2	Ω
9 <sub>FS</sub>	Forward Transconductance			$V_{DS} = 20V, I_D = 4A$		-	6.3	-	S
C <sub>iss</sub> C <sub>oss</sub>	Input Ca	acteristics ut Capacitance tput Capacitance		/ <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V		-	565 80	735 105	pF pF
C <sub>rss</sub>		Transfer Capacitance	t	f = 1MHz			5	8	pF
Q <sub>g(tot)</sub>	Total Ga	ate Charge at 10V	1	$V_{DS} = 400V, I_D = 6.5A$ $V_{GS} = 10V$ (Note 4)		-	14	18	nC
Q <sub>gs</sub>	Gate to	Source Gate Charge	Ň			-	4	-	nC
Q <sub>gd</sub>	Gate to	Drain "Miller" Charge				-	6	-	nC
Switching	Charac	teristics			·				
t <sub>d(on)</sub>	-	Delay Time		/ 050)/ L 0.54		-	17	45	ns
t <sub>r</sub>	Turn-On Rise Time			$V_{DD} = 250V, I_D = 6.5A,$ $V_{GS} = 10V, R_G = 25\Omega$		-	34	80	ns
t <sub>d(off)</sub>	Turn-Off	Delay Time		(Note 4)		-	43	95	ns
t <sub>f</sub>	Turn-Off	Fall Time				/	27	60	ns
Drain-Sou	ce Dioc	le Characteristics			ł		1	I	
I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current				-	-	6.5	Α	
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode F		e Diode Forwa	Forward Current		-	-	26	Α
V <sub>SD</sub>	Drain to	Source Diode Forward	Voltage $V_{GS} = 0V, I_{SD} = 6.5A$			-	-	1.6	V
t <sub>rr</sub>	Reverse	Recovery Time		/ <sub>GS</sub> = 0V, I <sub>SD</sub> = 6.5A		-	50	-	ns
Q <sub>rr</sub>	Reverse	Recovery Charge	d	$dI_F/dt = 100A/\mu s$		-	0.05		μC

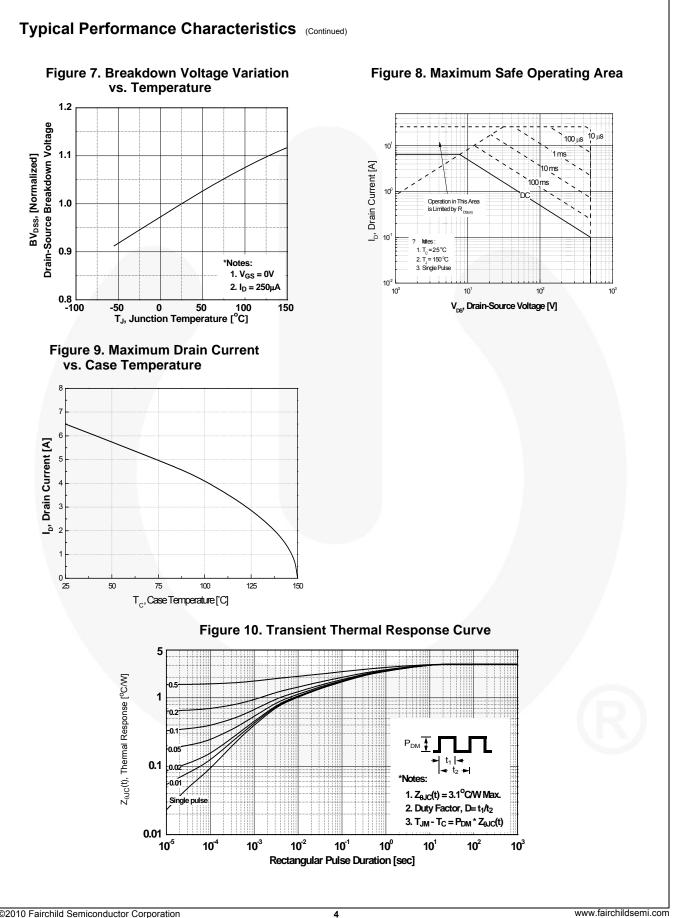
 $\begin{aligned} 3.I_{SD} &\leq 6.5 \text{ A}, \text{ di/dt} \leq 200 \text{ A/}\mu\text{s}, \text{ V}_{DD} \leq \text{BV}_{DSS}, \text{ starting } \text{T}_{\text{J}} = 25^{\circ}\text{C}. \end{aligned}$   $4. \text{ Essentially independent of operating temperature typical characteristics}. \end{aligned}$ 

### 2



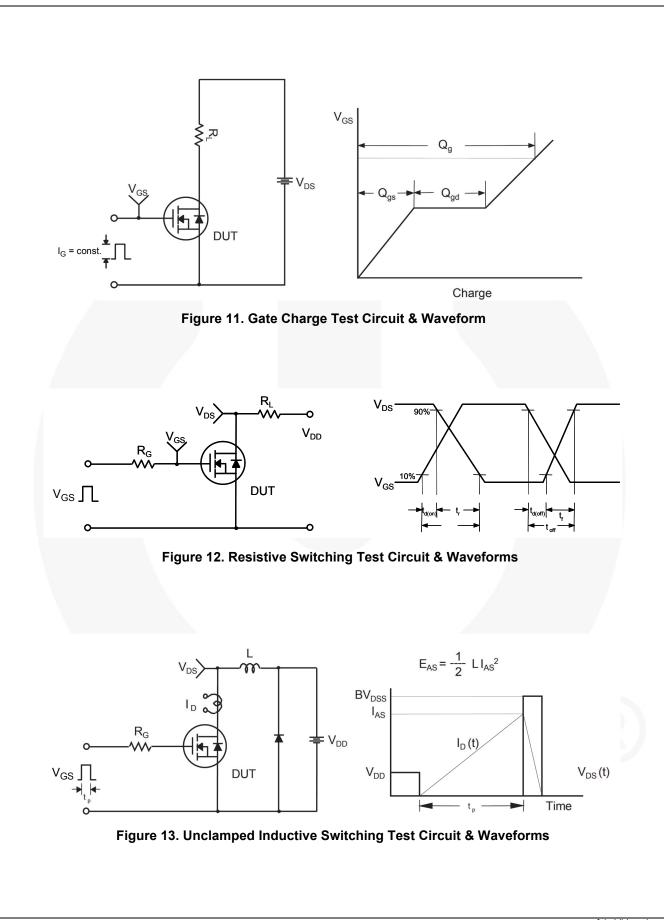


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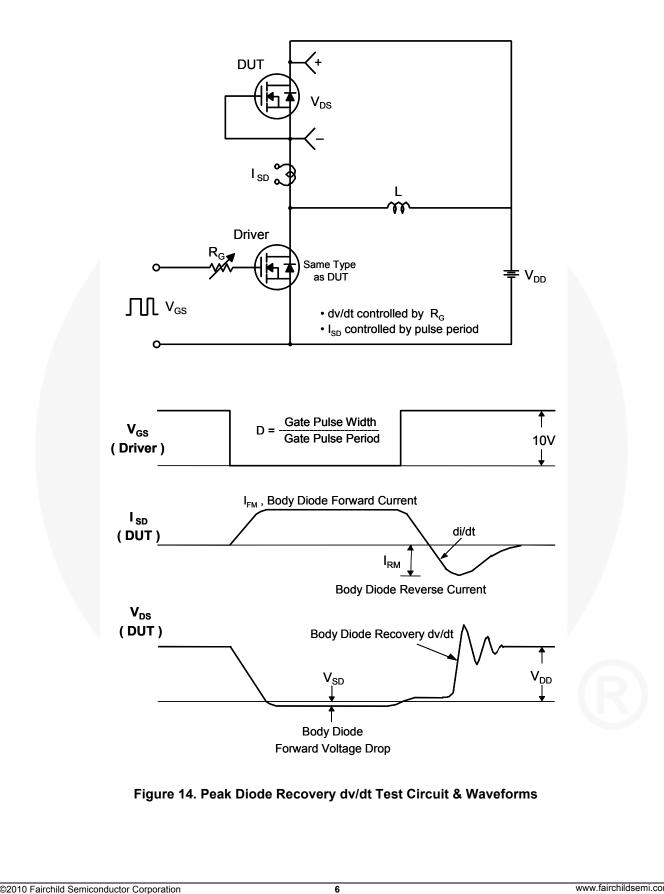


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FDPF8N50NZU — N-Channel UniFET<sup>TM</sup> Ultra FRFET<sup>TM</sup> MOSFET

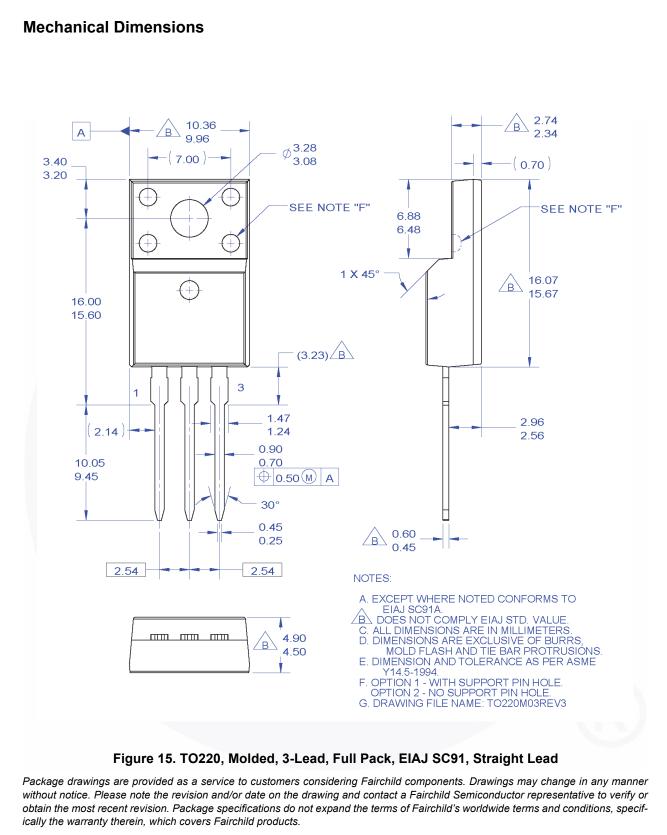


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